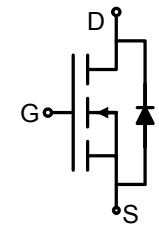
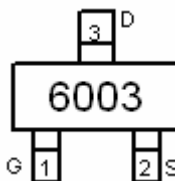
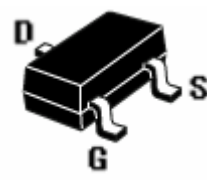


| | |
|---|--|
| <p>Description</p> <p>The NCE6003Y uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other switching application.</p> <p>General Features</p> <ul style="list-style-type: none"> ● $V_{DS} = 60V, I_D = 3A$ $R_{DS(ON)} < 105m\Omega @ V_{GS}=10V$ $R_{DS(ON)} < 125m\Omega @ V_{GS}=4.5V$ ● High power and current handling capability ● Lead free product is acquired ● Surface mount package <p>Application</p> <ul style="list-style-type: none"> ● Battery switch ● DC/DC converter | <div style="text-align: center;">  <p>Schematic Diagram</p>  <p>Marking and Pin Assignment</p>  <p>SOT-23 -3L Top View</p> </div> |
|---|--|

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|------------|
| 6003 | NCE6003Y | SOT-23-3L | Ø180mm | 8 mm | 3000 units |

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|------------|------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Gate-Source Voltage | V_{GS} | ±20 | V |
| Drain Current-Continuous | I_D | 3 | A |
| Drain Current-Pulsed ^(Note 1) | I_{DM} | 10 | A |
| Maximum Power Dissipation | P_D | 1.7 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | °C |

Thermal Characteristic

| | | | |
|---|-----------------|------|------|
| Thermal Resistance, Junction-to-Ambient ^(Note 2) | $R_{\theta JA}$ | 73.5 | °C/W |
|---|-----------------|------|------|

Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---------------------------------|------------|---------------------------|-----|-----|-----|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 60 | 65 | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=60V, V_{GS}=0V$ | - | - | 1 | μA |

| | | | | | | |
|--|--------------|---|-----|------|-----------|------------|
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | - | - | ± 100 | nA |
| On Characteristics ^(Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 1.0 | 1.2 | 1.9 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=3A$ | - | 78 | 105 | m Ω |
| | | $V_{GS}=4.5V, I_D=3A$ | - | 95 | 125 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS}=15V, I_D=2A$ | 3 | - | - | S |
| Dynamic Characteristics ^(Note 4) | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=30V, V_{GS}=0V,$ $F=1.0MHz$ | - | 247 | - | PF |
| Output Capacitance | C_{oss} | | - | 34 | - | PF |
| Reverse Transfer Capacitance | C_{rss} | | - | 19.5 | - | PF |
| Switching Characteristics ^(Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=30V, I_D=1.5A$ $V_{GS}=10V, R_{GEN}=1\Omega$ | - | 6 | - | nS |
| Turn-on Rise Time | t_r | | - | 15 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 15 | - | nS |
| Turn-Off Fall Time | t_f | | - | 10 | - | nS |
| Total Gate Charge | Q_g | $V_{DS}=30V, I_D=3A,$ $V_{GS}=4.5V$ | - | 6 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 1 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 1.3 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage ^(Note 3) | V_{SD} | $V_{GS}=0V, I_S=3A$ | - | - | 1.2 | V |
| Diode Forward Current ^(Note 2) | I_S | | - | - | 3 | A |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

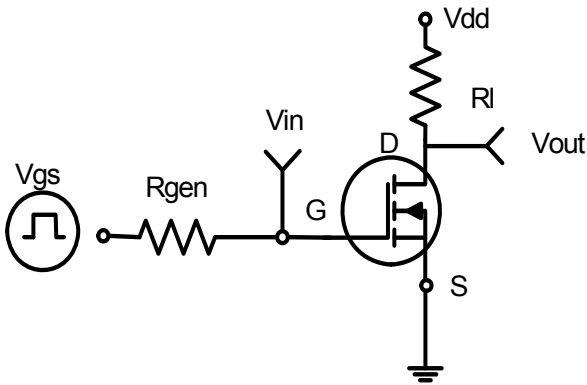


Figure 1: Switching Test Circuit

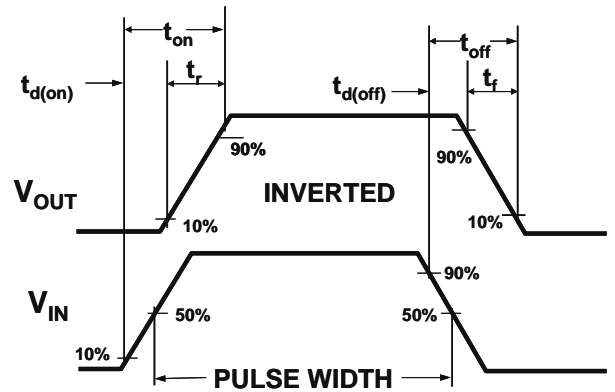


Figure 2: Switching Waveforms

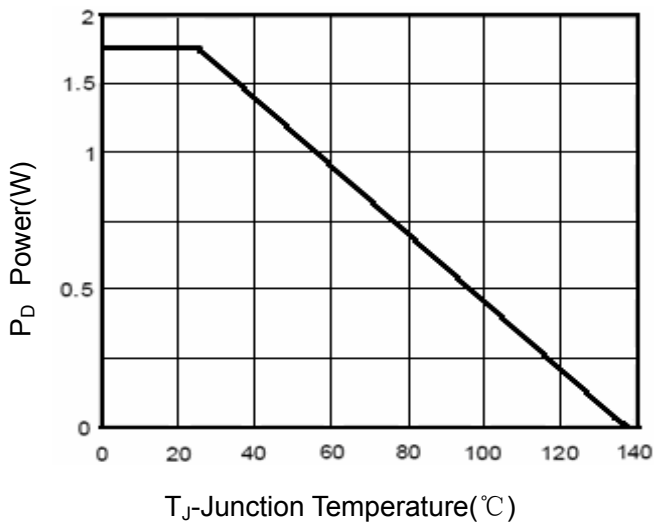


Figure 3 Power Dissipation

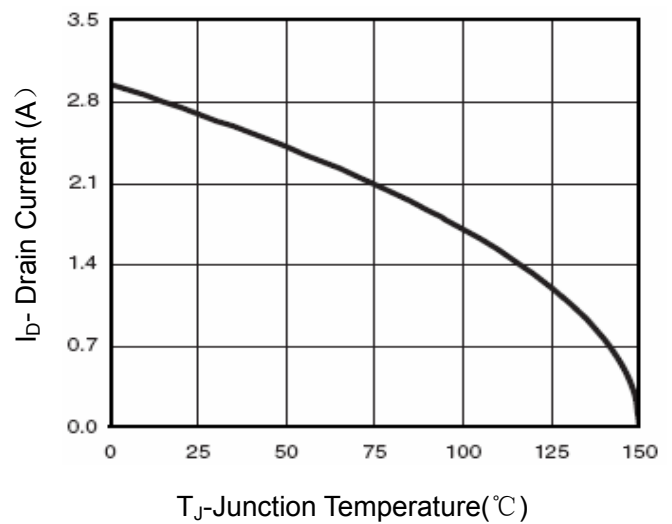


Figure 4 Drain Current

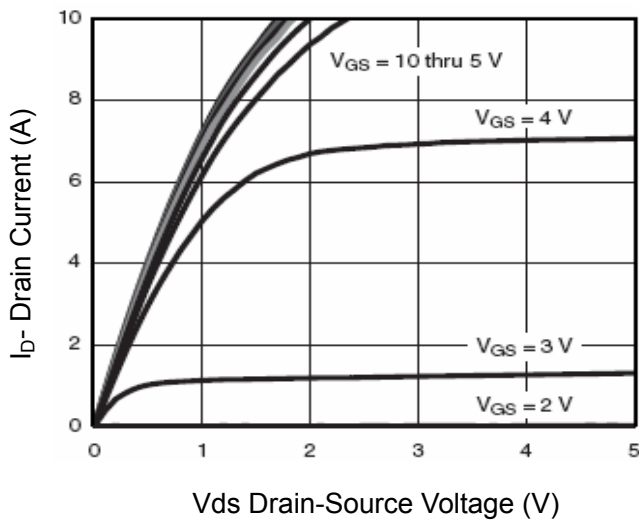


Figure 5 Output Characteristics

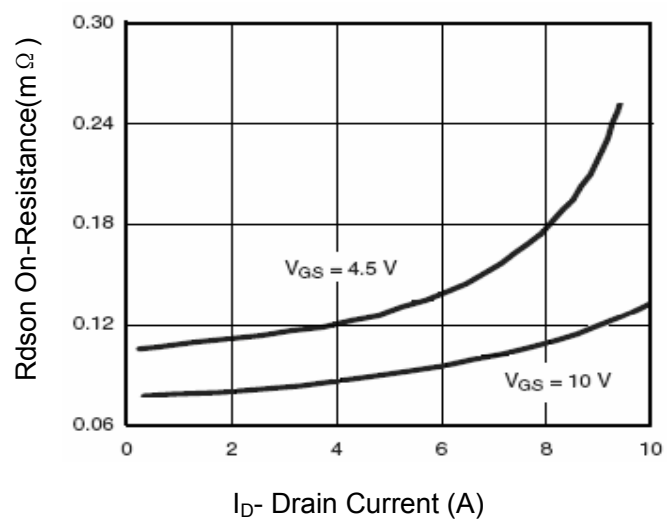


Figure 6 Drain-Source On-Resistance

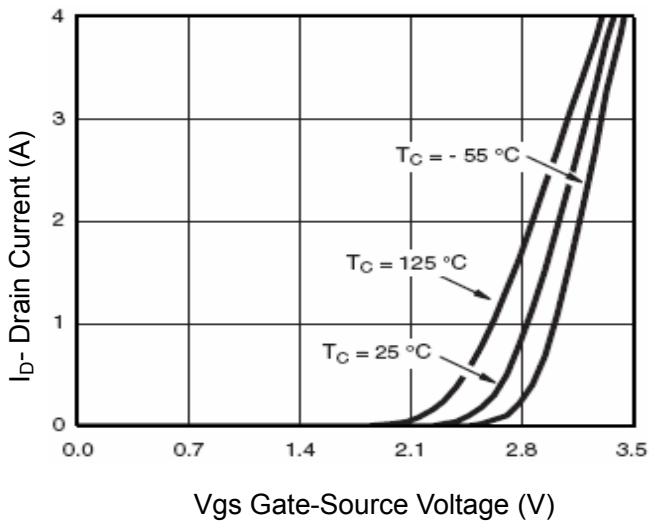


Figure 7 Transfer Characteristics

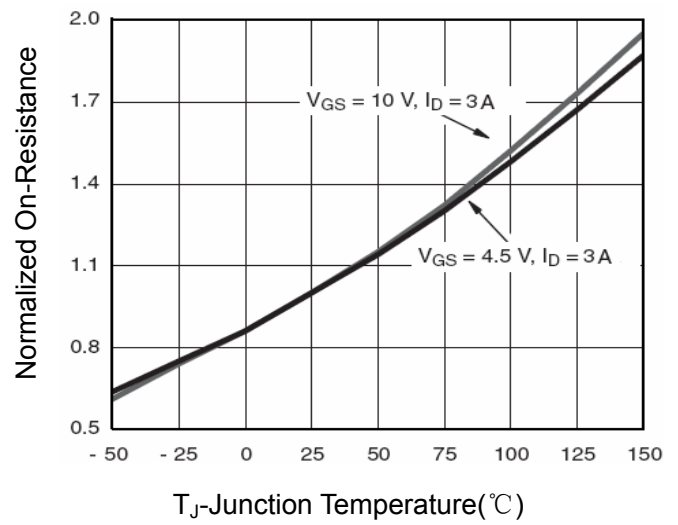


Figure 8 Drain-Source On-Resistance

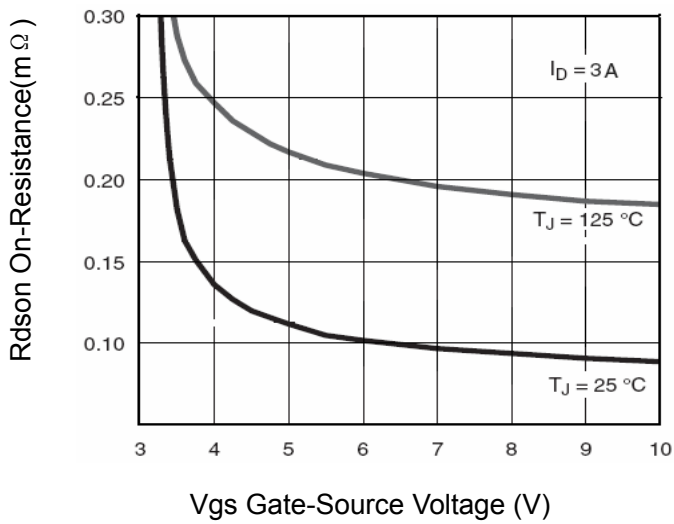


Figure 9 Rdson vs Vgs

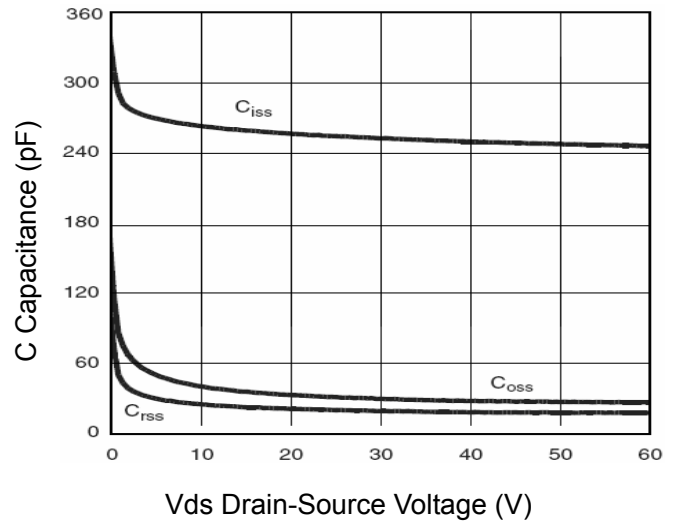


Figure 10 Capacitance vs Vds

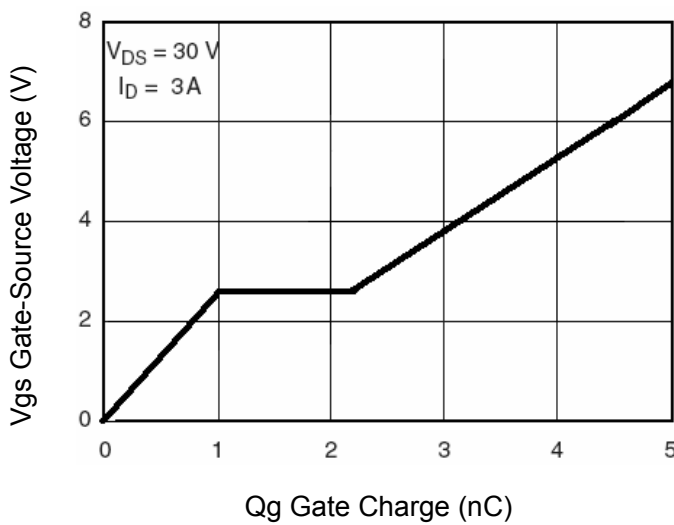


Figure 11 Gate Charge

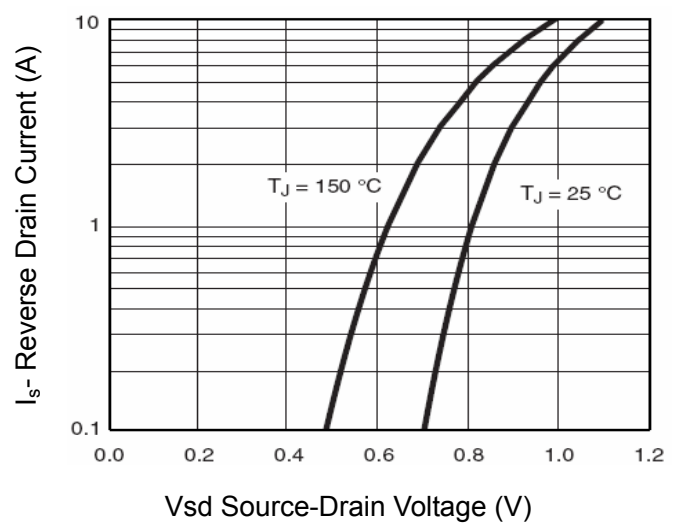


Figure 12 Source- Drain Diode Forward

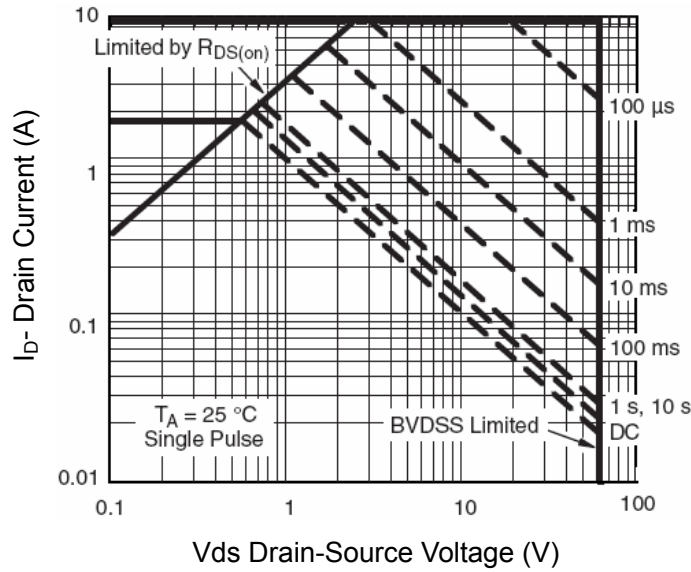


Figure 13 Safe Operation Area

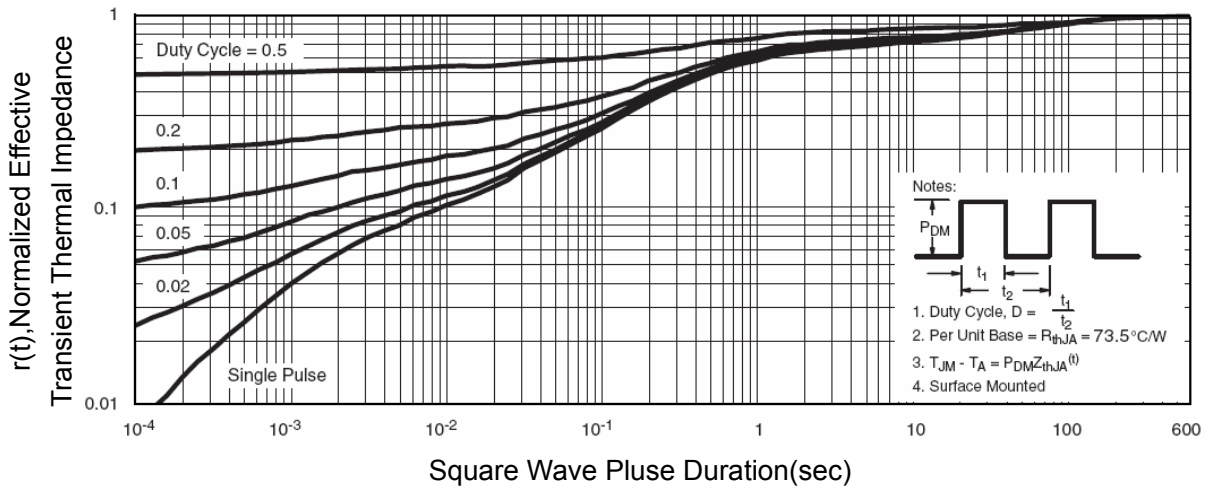
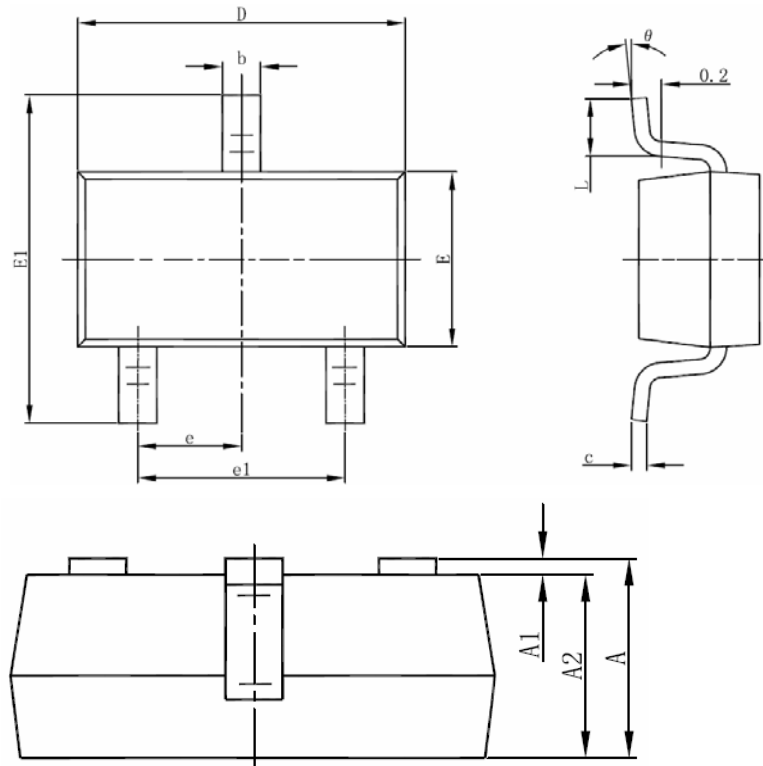


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23-3L Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E | 1.500 | 1.700 | 0.059 | 0.067 |
| E1 | 2.650 | 2.950 | 0.104 | 0.116 |
| e | 0.950(BSC) | | 0.037(BSC) | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| θ | 0° | 8° | 0° | 8° |

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.